

SOT-23-3L Plastic-Encapsulate MOSFETS

Features

- $V_{DS}=100V$
- $I_D=2.5A$
- $R_{DS(on)}@V_{GS}=10V < 160m\Omega$
- $R_{DS(on)}@V_{GS}=4.5V < 170m\Omega$
- Advanced trench technology
- Fast Switching Speedze

Drain-source Voltage
100 V
Drain Current
2.5 Ampere

Applications

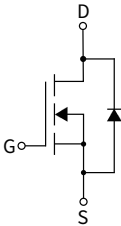
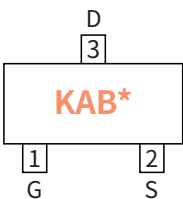
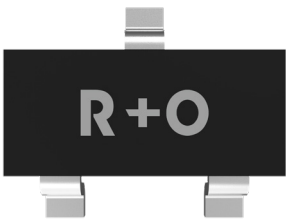
- PWM application
- Load switching
- Power management

Mechanical Data

- Case: SOT-23-3L
Molding compound meets UL 94V-0 flammability rating, RoHS-compliant,halogen-free
- Terminals: Solder plated, solderable per MIL-STD-750,Method 2026

Function Diagram

SOT-23-3L



Ordering Information

PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23-3L	R1	0.0132	3000	30000	300000	7"

Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	VALUE
Drain-source Voltage		V_{DS}	V	100
Gate-source Voltage		V_{GS}	V	± 20
Drain Current	$T_A=25^{\circ}C$ @ Steady State	I_D	A	2.5
Pulsed Drain Current		I_{DM}	A	7
Total Power Dissipation @ $T_A=25^{\circ}C$		P_D	mW	1300
Thermal Resistance Junction-to-Ambient @ Steady State ⁽¹⁾		$R_{\theta JA}$	$^{\circ}C / W$	99
Junction and Storage Temperature Range		T_J, T_{STG}	$^{\circ}C$	-55 ~+150

● Static Parameter Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	V	100	—	—
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	μA	—	—	1.0
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	nA	—	—	± 100
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	V	1..0	2.0	2.5
Static Drain-Source On-Resistance ⁽²⁾	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.5A$	m Ω	—	73	160
		$V_{GS}=4.5V, I_D=2A$		—	97	170

● Dynamic Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$	pF	—	290	—
Output Capacitance	C_{oss}			—	117	—
Reverse Transfer Capacitance	C_{rss}			—	31	—

● Switching Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Total Gate Charge	Q_g	$V_{GS}=4.5V$ $V_{DS}=50V$ $I_D=2.5A$	nC	—	2.5	—
Gate-Source Charge	Q_{gs}			—	0.5	—
Gate-Drain Charge	Q_{gd}			—	1.2	—
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=4.5V$ $V_{DS}=50V$ $R_G=6.8\Omega$ $I_D=1A$	ns	—	2.2	—
Turn-on Rise Time	t_r			—	2.1	—
Turn-off Delay Time	$t_{D(off)}$			—	9	—
Turn-off fall Time	t_f			—	3.6	—

● Drian-Source Diode Characteristics

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Diode Forward Voltage ⁽²⁾	V_{SD}	$I_S=2.5A, V_{GS}=0V$	V	—	—	1.3
Maximum Body-Diode Continuous Current ⁽³⁾	I_S	—	A	—	—	2.5
Reverse Recovery Time ⁽²⁾	T_{rr}	$I_S=1.1A, di/dt=100A/us,$ $T_J=25^\circ C$	nS	—	20	—
Reverse Recovery Charge ⁽²⁾	Q_{rr}		nC	—	13	—

Note:(1)Surface mounted on 1 in square Cu board.

(2)Pulse with $\leq 400\mu s$;duty cycle $\leq 2\%$.

(3)Repetitive rating;pulse with limited by max. junction temperature.

● Package Outline Dimensions (SOT-23-3L)

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.05	1.25	0.041	0.049
A1	-	0.10	-	0.004
A2	1.05	1.15	0.041	0.045
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.82	3.02	0.111	0.119
E	1.50	1.70	0.059	0.067
E1	2.65	2.95	0.104	0.116
e	0.90	1.00	0.035	0.039
e1	1.80	2.00	0.071	0.079
L	0.45	0.65	0.018	0.026
L1	0.30	0.60	0.012	0.024
θ	-	8°	-	8°

● Suggested Pad Layout

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.80	-	0.031	-
K	-	0.95	-	0.037
M	2.00	-	0.078	-
N	-	2.0	-	0.079